

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2001-172767

(43)Date of publication of application : 26.06.2001

(51)Int.Cl. C23C 16/40  
C23C 16/02  
C23C 16/18  
H01L 21/316

(21)Application number : 2000-315409

(71)Applicant : ASM MICROCHEMISTRY OY

(22)Date of filing : 16.10.2000

(72)Inventor : RITALA MIKKO  
RAHTU ANTTI  
LESKELAE MARKKU  
KUKLI KAUPPO

(30)Priority

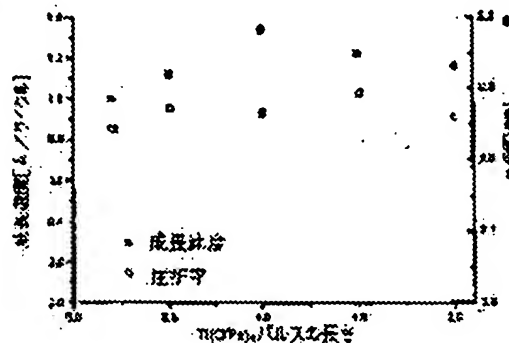
Priority number : 1999 992223 Priority date : 14.10.1999 Priority country : FI

## (54) METHOD OF GROWING OXIDE THIN FILM

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a method of growing an oxide thin film on a substrate.

SOLUTION: In the method of growing an oxide thin film according to the principle of the ALD method where an oxide thin film is deposited onto a substrate by an alternating surface reaction of metallic raw material and oxygen raw material, the oxygen raw material to be used is composed of a compound of boron, silicon or metal having at least one organic ligand, and the oxygen is combines with at least one atom of boron, silicon or metal.



## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]